

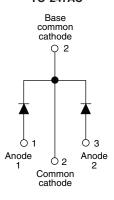


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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A

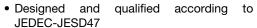




PRODUCT SUMMARY						
Package	TO-247AC					
I _{F(AV)}	2 x 16 A					
V_{R}	1200 V					
V _F at I _F	3.0 V					
t _{rr} typ.	30 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}









ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA32PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A per leg continuous current, the VS-HFA32PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA32PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V_R		1200	V			
Maximum continuous forward current per leg	1	T _C = 100 °C	16				
per device	l _F	1 _C = 100 C	32	^			
Single pulse forward current	I _{FSM}		190	А			
Maximum repetitive forward current	I _{FRM}		64				
Maximum navvar dissination	П	T _C = 25 °C	151				
Maximum power dissipation	P _D	T _C = 100 °C	60	°C			
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	W			



VS-HFA32PA120CPbF, VS-HFA32PA120C-N3

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	Ι _R = 100 μΑ	1200	ı	-			
		I _F = 16 A		-	2.5	3.0	V	
Maximum forward voltage	V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93		
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7		
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	0.75	20	μΑ	
leakage current	I _{RM}	T _J = 125 °C, V _R = 0.8 x V _R rated	See fig. 2	-	375	2000		
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	27	40	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V _R = 30 V	-	30	-		
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	90	135	ns	
000 lig. 5, 10	t _{rr2}	T _J = 125 °C	I_F = 16 A dI_F/dt = 200 A/ μ s V_R = 200 V	-	164	245		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	5.8	10	A nC	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675		
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	IIC	
Peak rate of fall of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	-	A/µs	
current during t _b See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	0.83				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-				
Weight			-	2.0	-	g			
vveignt			-	0.07	-	OZ.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AC (JEDEC)	HFA32PA120C						

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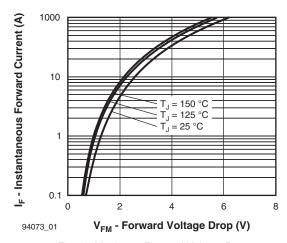


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

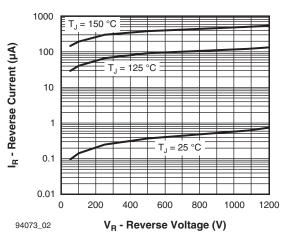


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

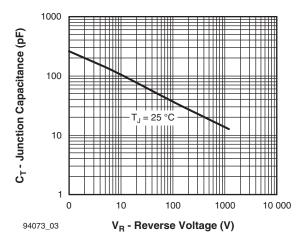


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

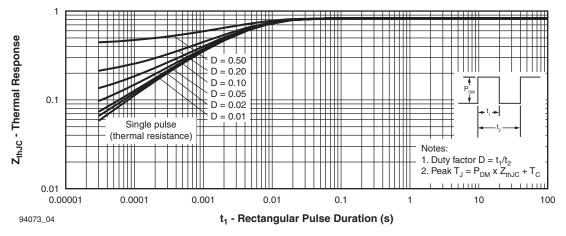


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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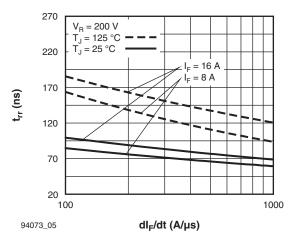


Fig. 5 - Typical Reverse Recovery Time vs. dl_E/dt (Per Leg)

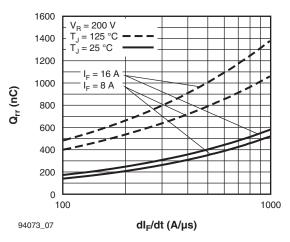


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

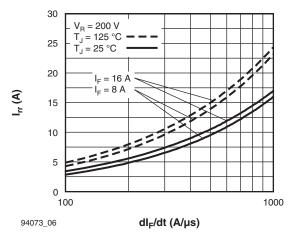


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

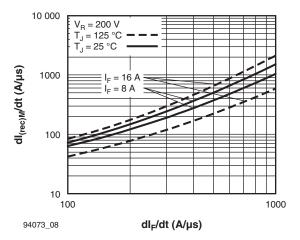


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

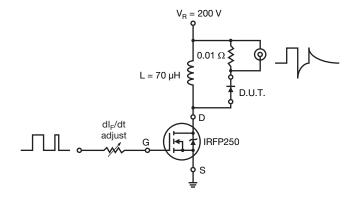
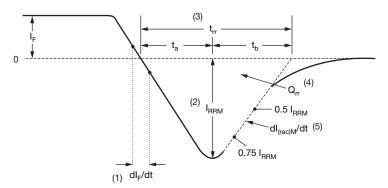


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA32PA120CPbF, VS-HFA32PA120C-N3

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

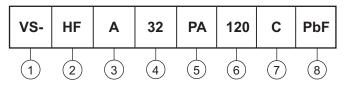
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- Electron irradiated
- Current rating (32 = 32 A)
- **5** PA = TO-247AC
- 6 Voltage rating: (120 = 1200 V)
- Circuit configuration

 C = Common cathode
- 8 Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-HFA32PA120CPbF	25	500	Antistatic plastic tube					
VS-HFA32PA120C-N3	25	500	Antistatic plastic tube					

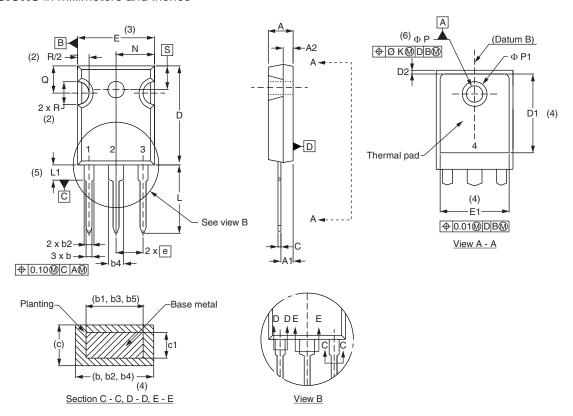
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?95542</u>							
Part marking information	TO-247ACPbF	www.vishay.com/doc?95226					
Part marking information	TO-247AC-N3	www.vishay.com/doc?95007					



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TO-247

DIMENSIONS in millimeters and inches



CVMPOL	SYMBOL MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIN	IETERS
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIBOL	MIN.	MAX.
Α	4.65	5.31	0.183	0.209		D2	0.51	1.35
A1	2.21	2.59	0.087	0.102		E	15.29	15.87
A2	1.17	1.37	0.046	0.054		E1	13.46	-
b	0.99	1.40	0.039	0.055		е	5.46	BSC
b1	0.99	1.35	0.039	0.053		ØK	0.254	
b2	1.65	2.39	0.065	0.094		L	14.20	16.10
b3	1.65	2.33	0.065	0.092		L1	3.71	4.29
b4	2.59	3.43	0.102	0.135		N	7.62	BSC
b5	2.59	3.38	0.102	0.133		ØΡ	3.56	3.66
С	0.38	0.89	0.015	0.035		Ø P1	-	7.39
c1	0.38	0.84	0.015	0.033		Q	5.31	5.69
D	19.71	20.70	0.776	0.815	3	R	4.52	5.49
D1	13.08	-	0.515	-	4	S	5.51	BSC

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
Е	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	=.	
е	5.46 BSC		0.215	0.215 BSC	
ØK	0.2	254	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0	.3	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	ı	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217	'BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

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